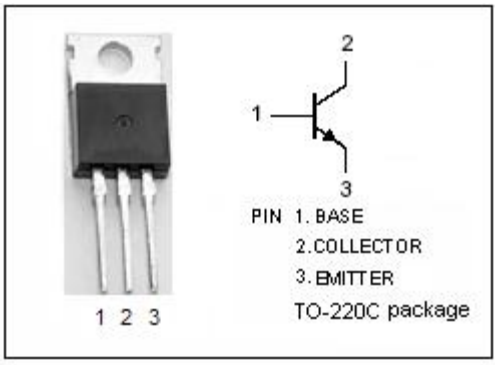
SPTECH Silicon NPN Power Transistor

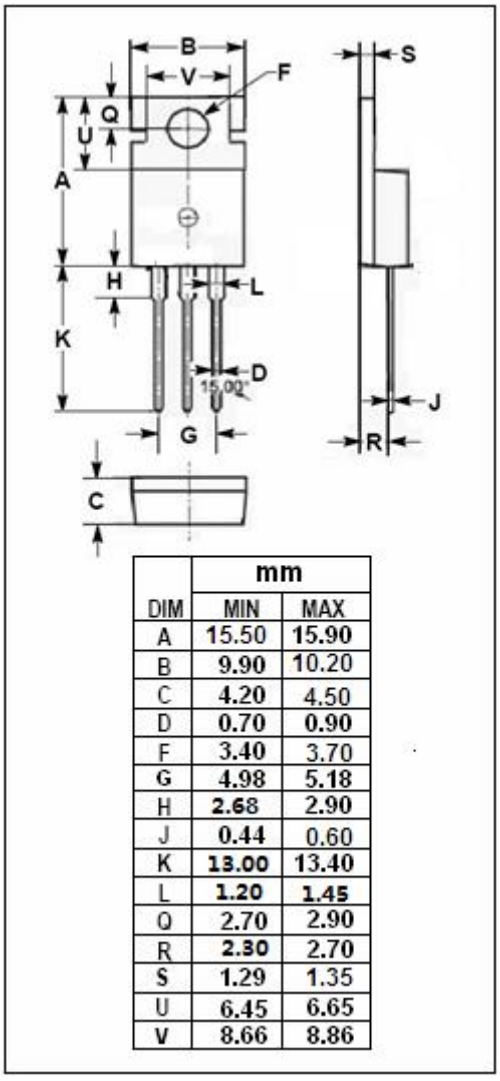


DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  :$V_{(BR)CEO}$= 150V(Min)
- Wide Area of Safe Operation
- Complement to Type 2SA940

APPLICATIONS

- Power amplifier applications.
- Vertical output applications.



DIM	mm MIN	MAX
A	15.50	15.90
B	9.90	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	13.00	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	150	V
V_{CEO}	Collector-Emitter Voltage	150	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	1.5	A
I_B	Base Current-Continuous	0.5	A
P_C	Collector Power Dissipation @ T_a=25℃	1.5	W
	Collector Power Dissipation @ T_C=25℃	25	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

SPTECH Silicon NPN Power Transistor

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 500mA; I_B= 50mA			1.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= 500mA ; V_{CE}= 10V			0.85	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 120V ; I_E= 0			10	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			10	μA
h_{FE}	DC Current Gain	I_C= 500mA ; V_{CE}= 10V	40		140	
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= 10V; f_{test}= 1MHz		35		pF
f_T	Current-Gain—Bandwidth Product	I_C= 500mA; V_{CE}= 10V		4		MHz